



App No.: 10/712,106
Inventor: Juitao Li et al.
Title: SILVER SELENIDE SPUTTER DEPOSITION DEFECT
FORMATION AND CONTROL
Docket No.: M4065.0706/P706

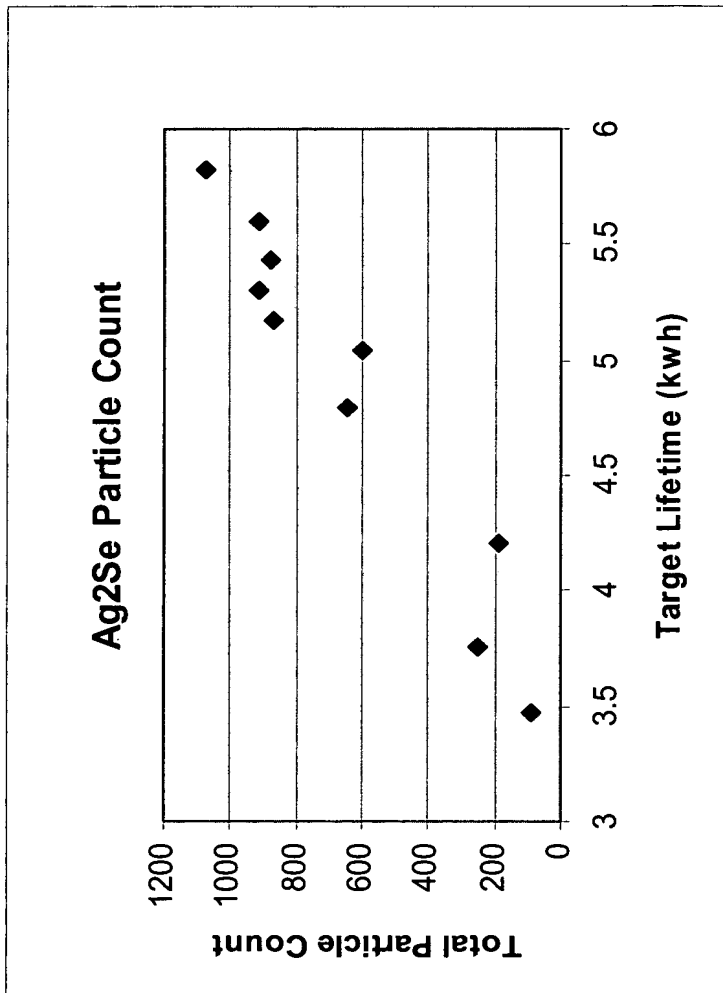


FIG. 1

FIG. 2(a)

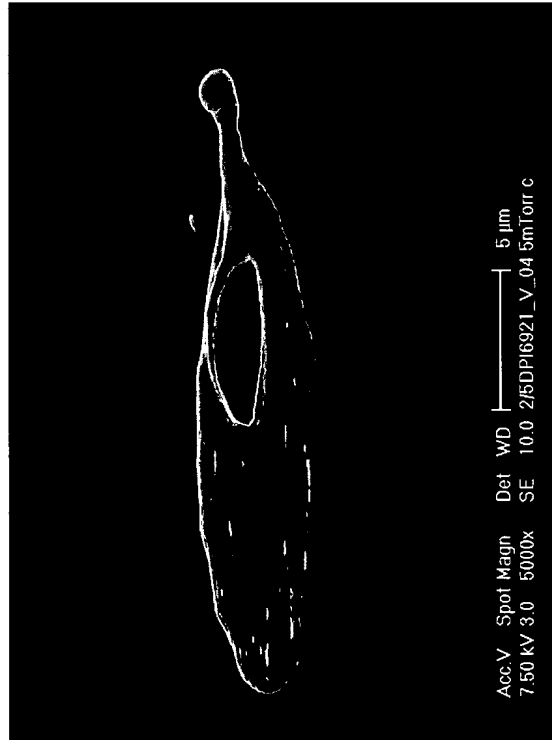
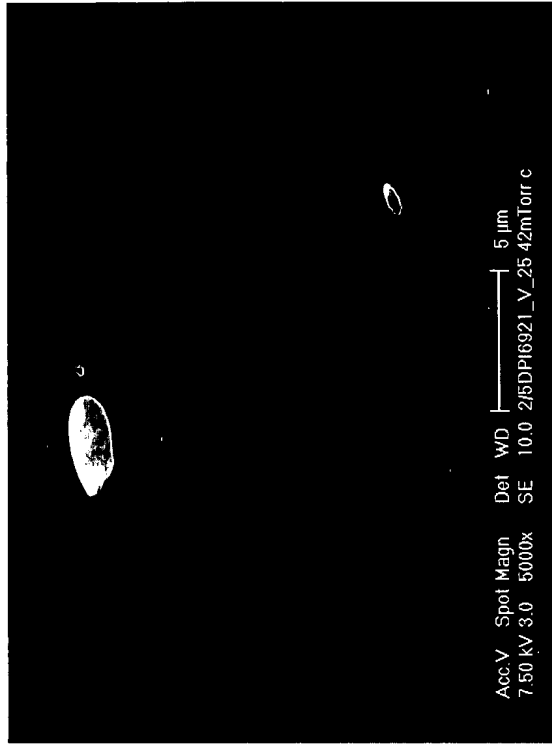


FIG. 2(b)



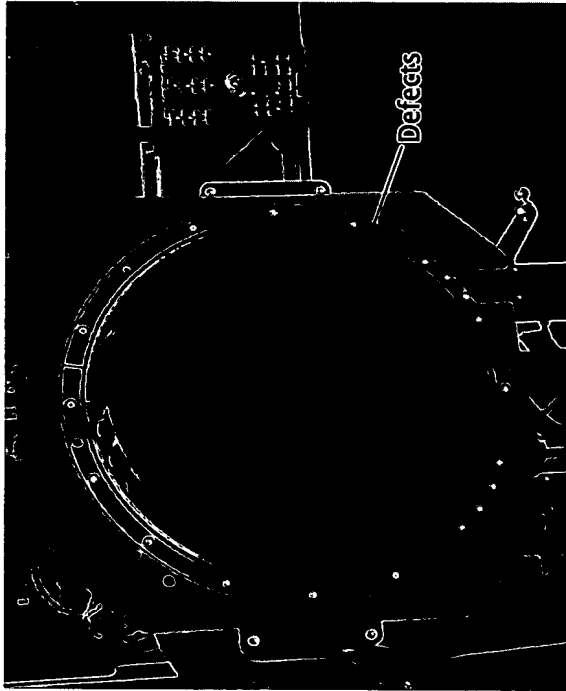


FIG. 3(a)

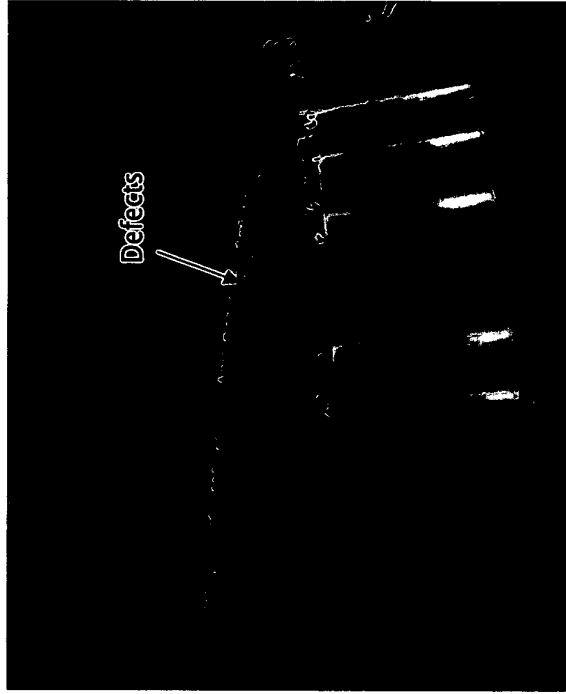


FIG. 3(b)

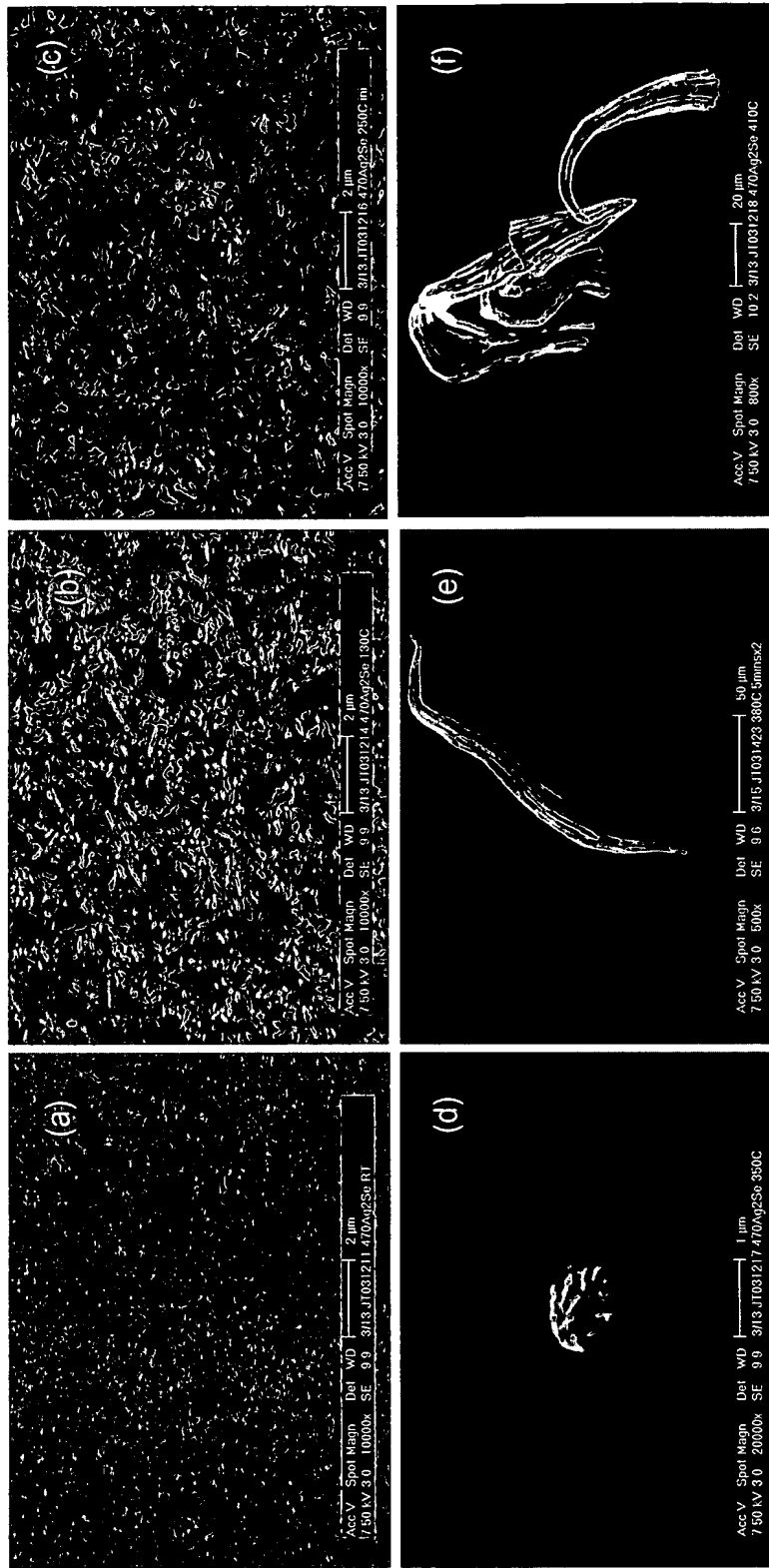


FIG. 4

Target Temperature vs. Sputter Power

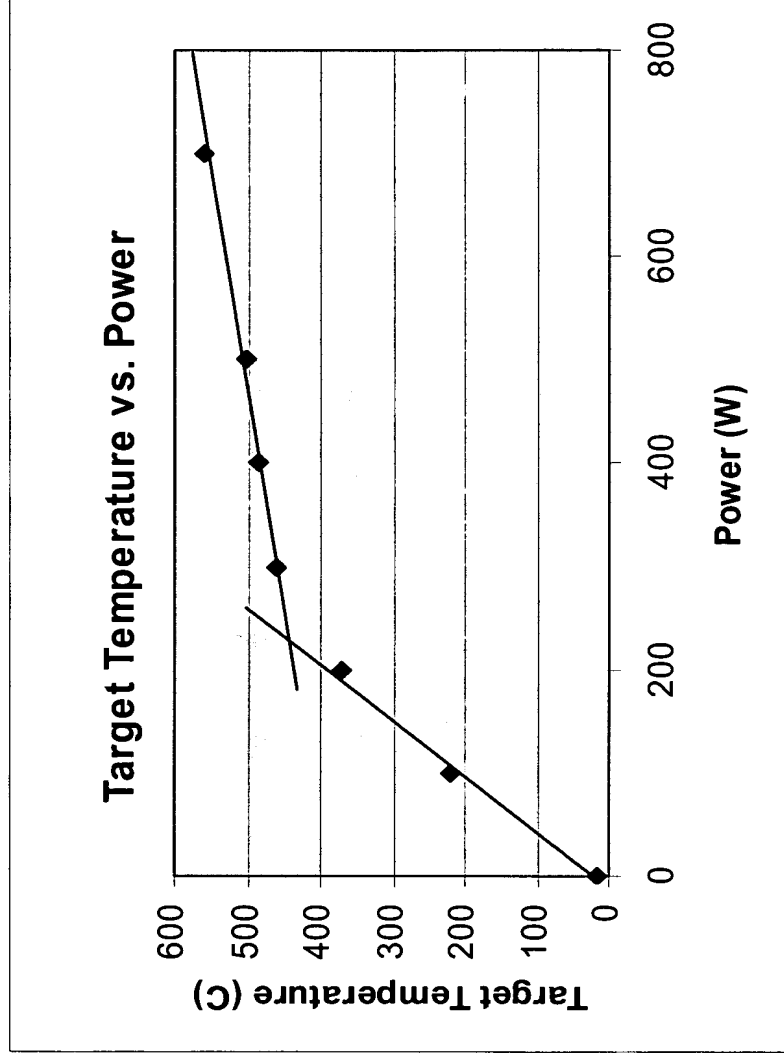


FIG. 5

Target Temperature vs. Sputter Pressure

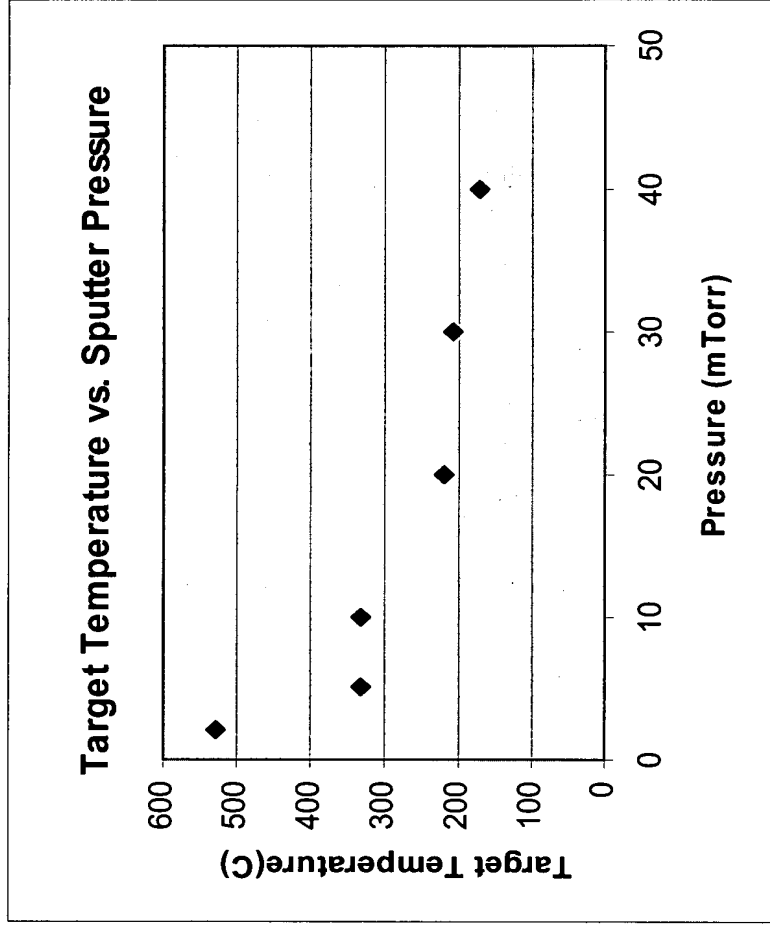


FIG. 6

Ne Sputtering Target Temperature

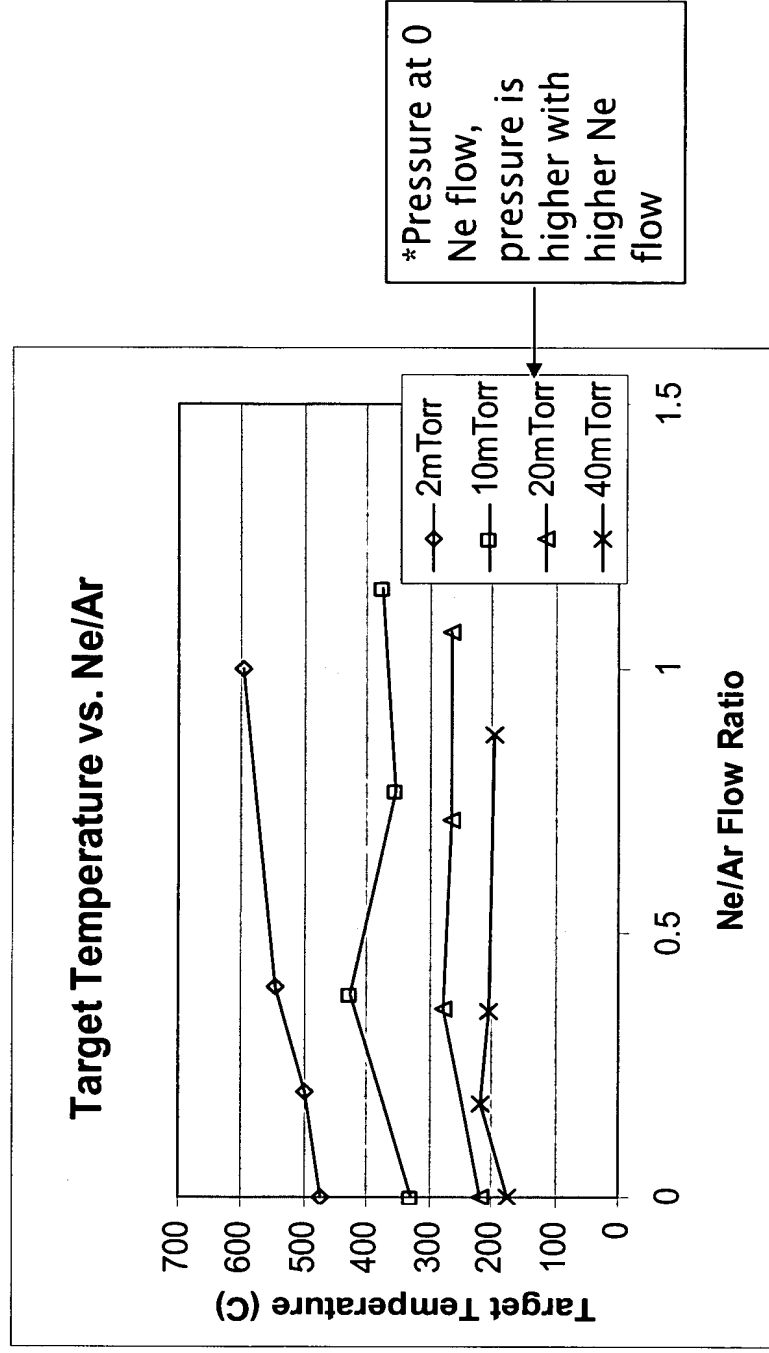


FIG. 7

Xe Sputtering Target Temperature

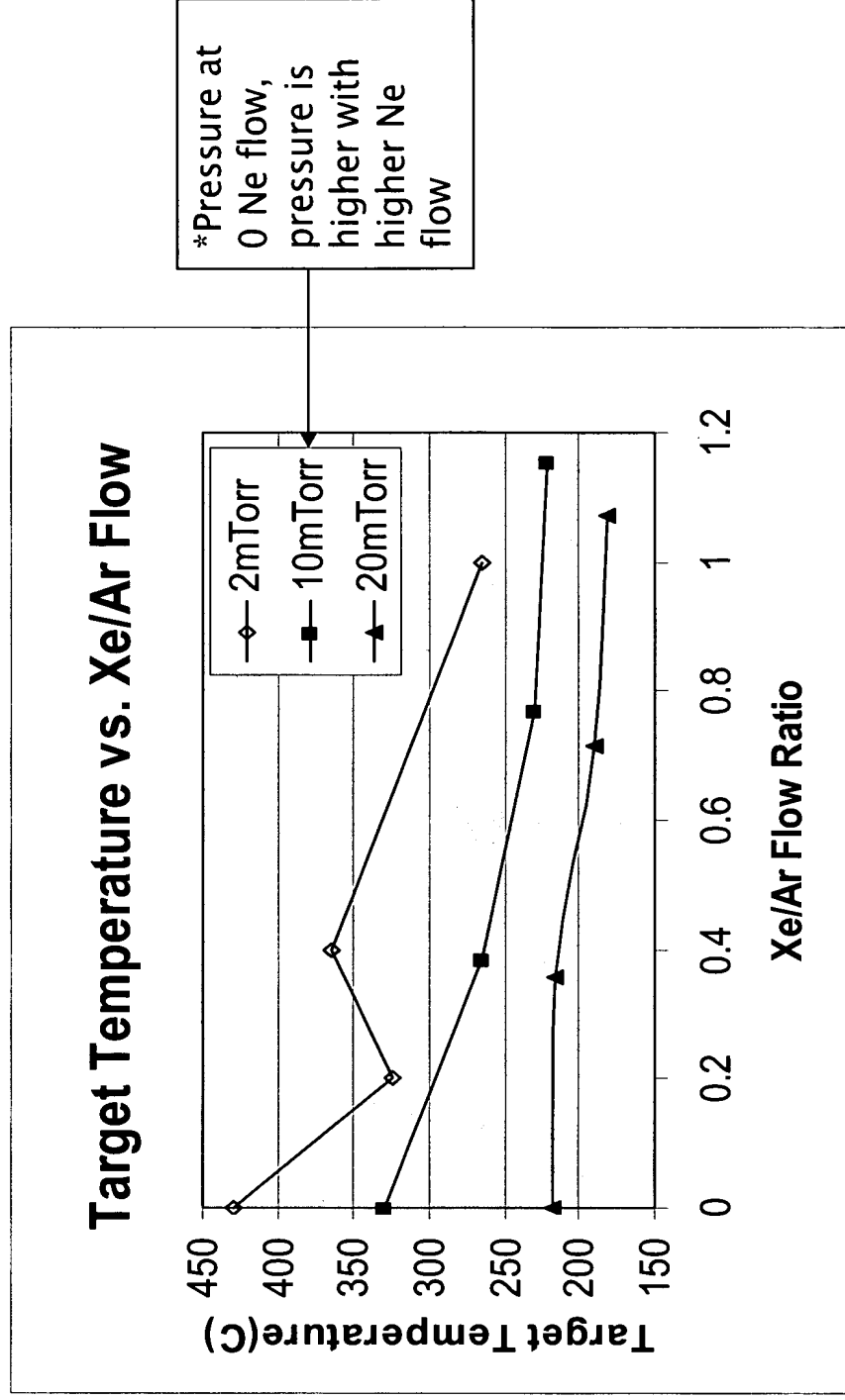


FIG. 8

Target Temperature vs. Sputter Gas

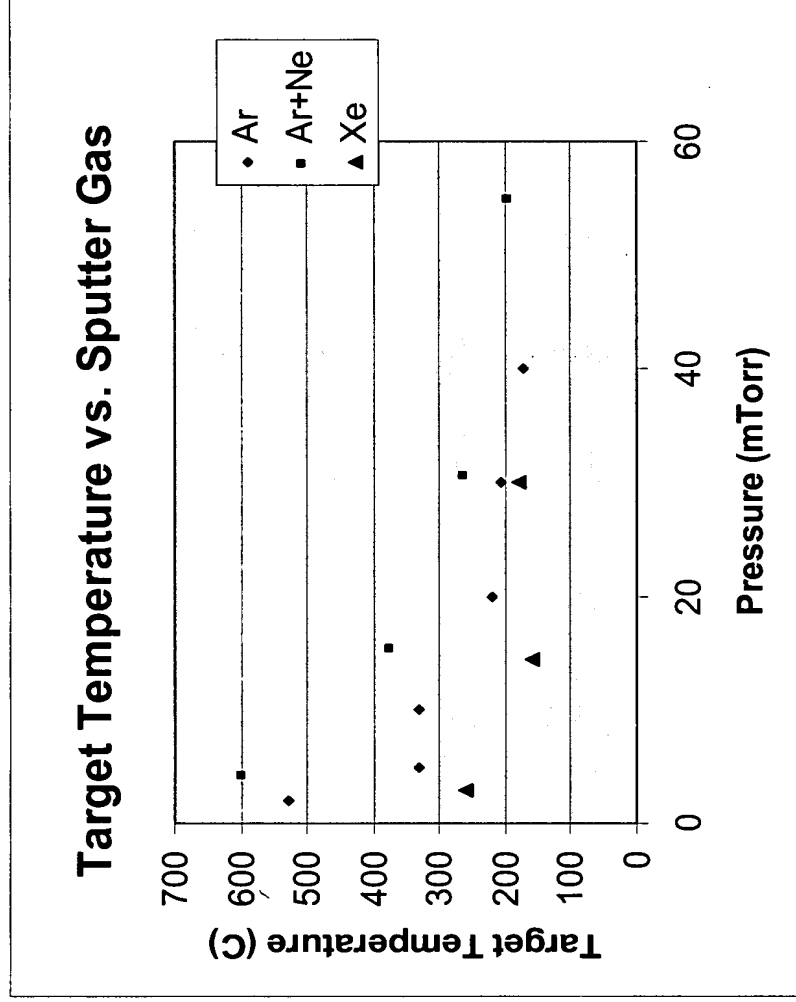


FIG. 9

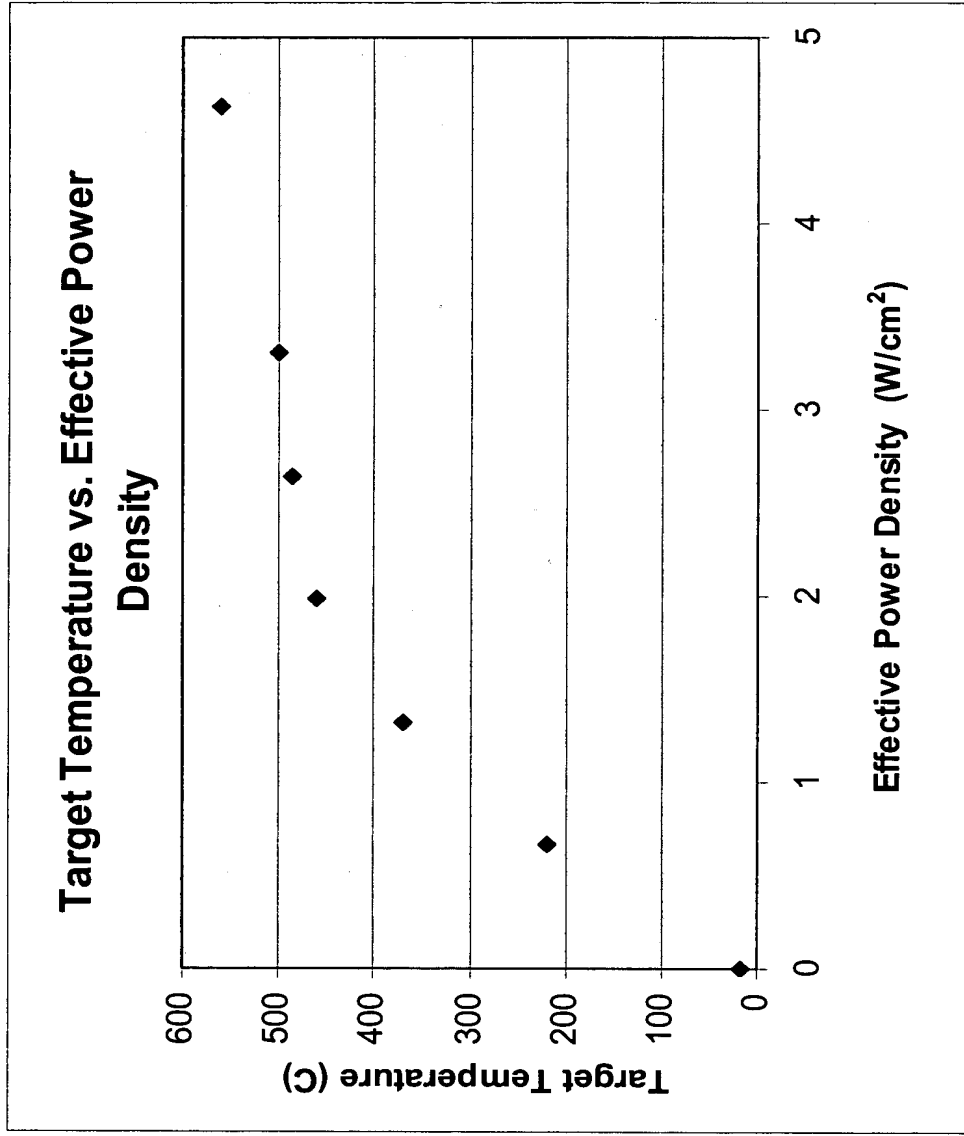


FIG. 10

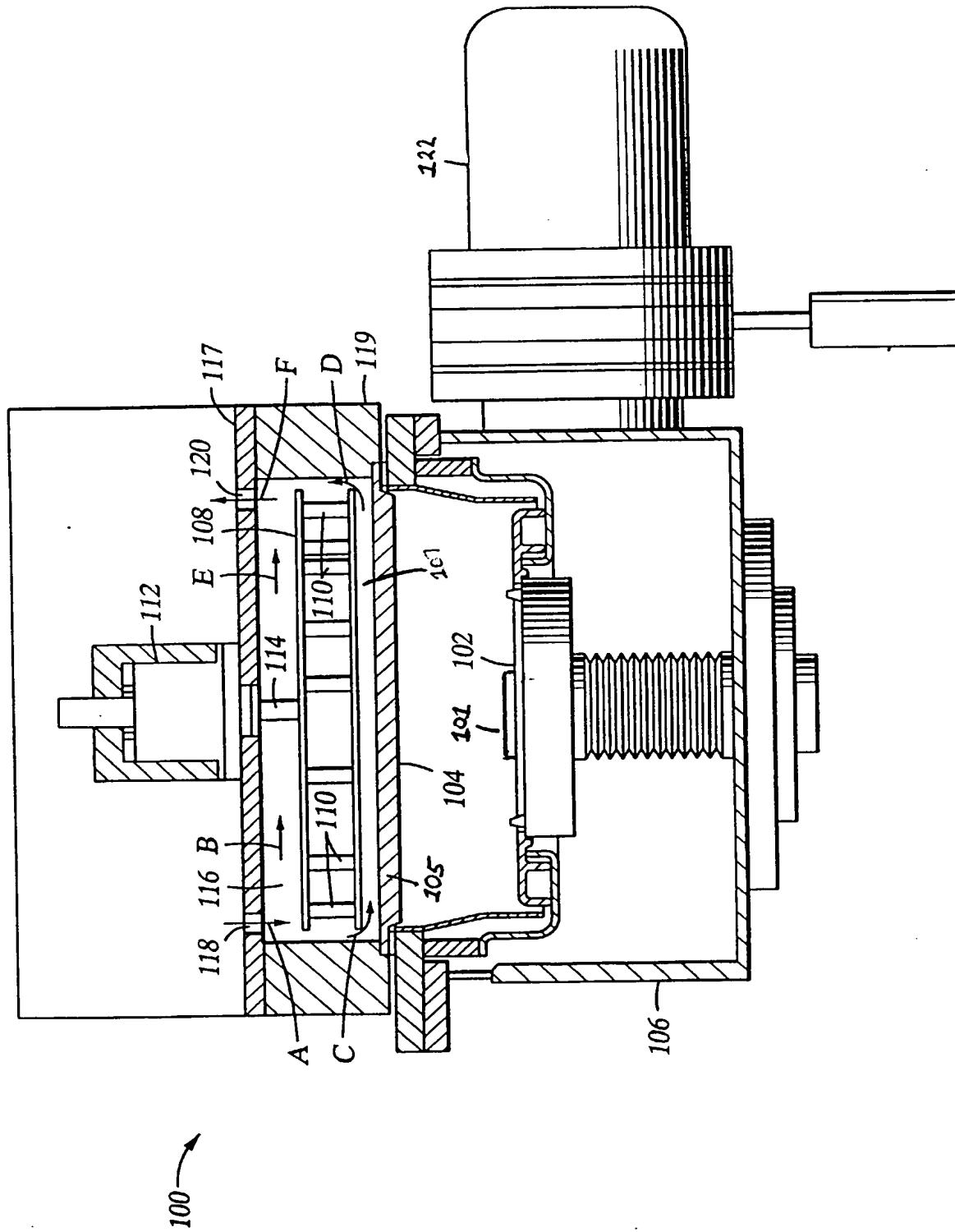


FIG. 11



FIG. 12(a)

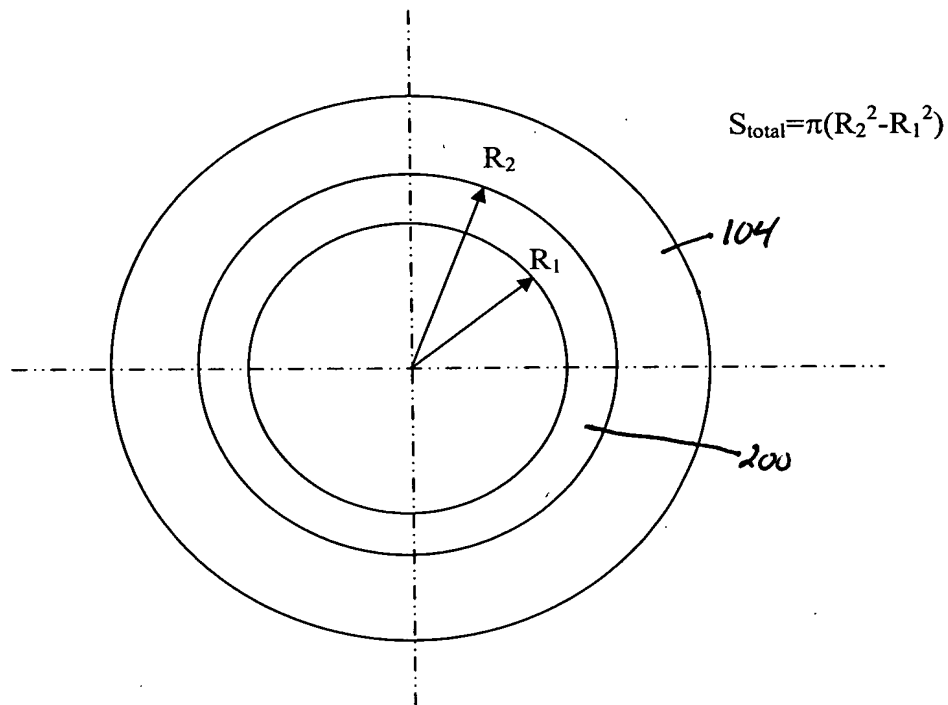


FIG. 12(b)

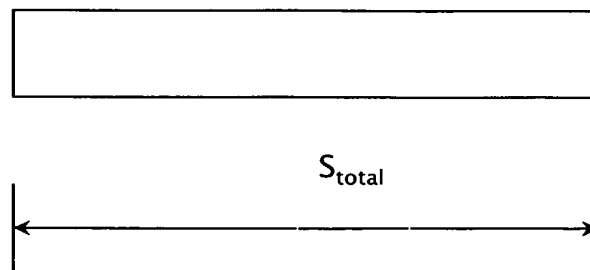
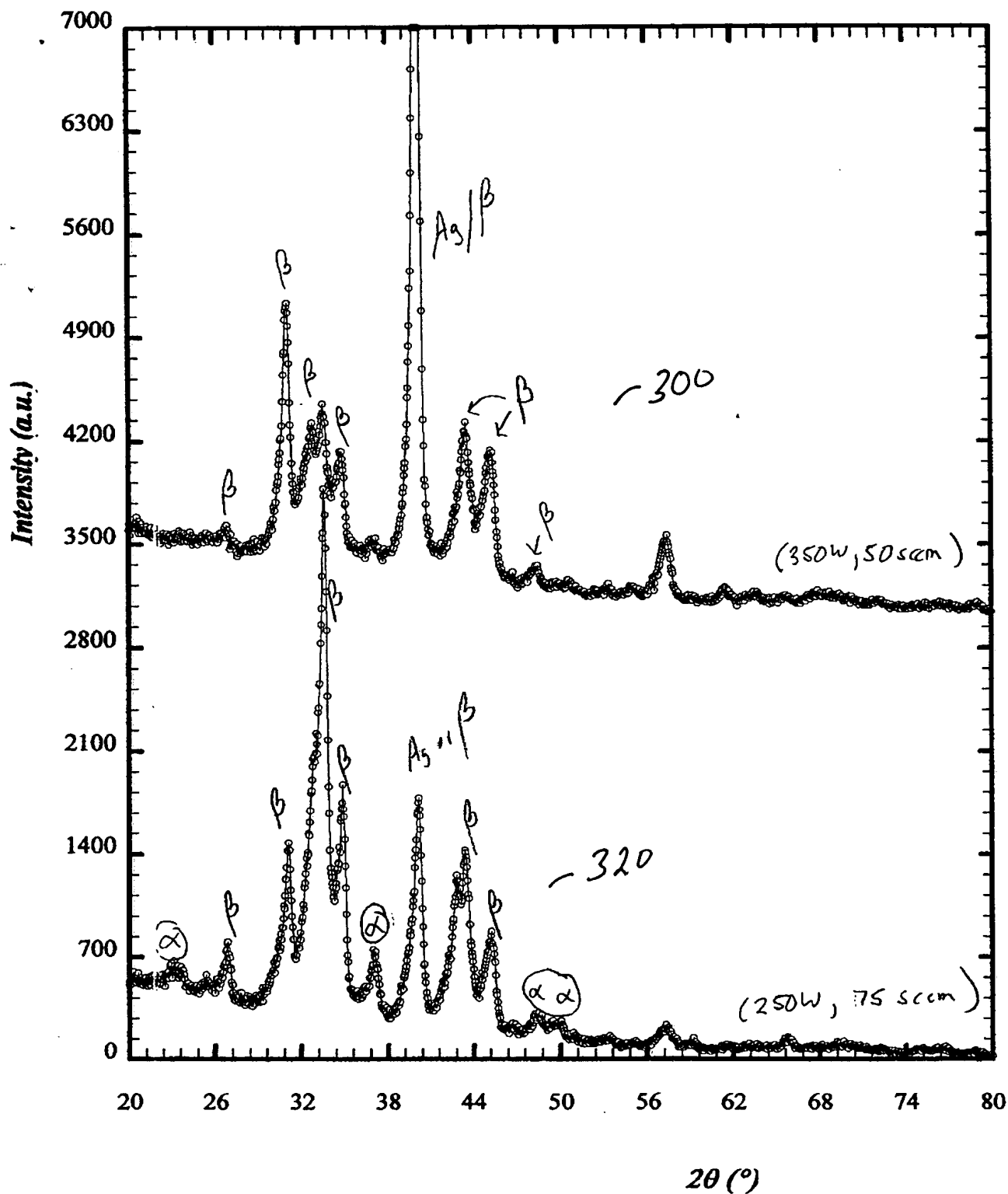


FIG. 12(c)

Ag₂Se on Ge₄Se₆



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Fig. 13